

Title Terms: MANUFACTURE; METHOD; MEMBRANE; FORMING; COMPOSITION;  
INTERLAYER; INSULATE; MEMBRANE; SEMICONDUCTOR; ELEMENT; ONE; KIND; SILANE  
; COMPOUND; HYDROLYSIS; PRESENCE; NITROGEN; ONIUM; SALT  
Derwent Class: A26; A85; E11; G02; L03; U11  
International Patent Class (Main): C09D-183/04  
International Patent Class (Additional): C09D-183/02; C09D-183/14  
File Segment: CPI; EPI

→ 1/5/2

DIALOG(R)File 352:Derwent WPI  
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WPI Acc No: 2002-133815/200218  
XRAM Acc No: C02-041195  
XRPX Acc No: N02-101222

Film for interlayer insulating film, used in semiconductor elements, has  
specific film density

Patent Assignee: JSR CORP (JAPS )  
Number of Countries: 001 Number of Patents: 001  
Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Week
JP 2001203197	A	20010727	JP 200012513	A	20000121	200218 B

Priority Applications (No Type Date): JP 200012513 A 20000121

Patent Details:

Patent No	Kind	Lan Pg	Main IPC	Filing Notes
JP 2001203197	A	20	H01L-021/312	

Abstract (Basic): JP 2001203197 A

NOVELTY - A film has a film density of 0.5 - 1.4 g/cm3.

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DETAILED DESCRIPTION - The film consists of formula (1).

x=1.3 - 1.9;

y=0.2 - 8.0;

z=0.6 - 7.0

USE - The method forms the film for an interlayer insulating film  
for use in a semiconductor element.

ADVANTAGE - The film has superior dielectric constant and  
mechanical strength.

pp: 20 DwgNo 0/0

Title Terms: FILM; INTERLAYER; INSULATE; FILM; SEMICONDUCTOR; ELEMENT;  
SPECIFIC; FILM; DENSITY

Derwent Class: A82; A85; G02; L03; U11

International Patent Class (Main): H01L-021/312

International Patent Class (Additional): C09D-005/25; C09D-183/06;  
H01L-021/316

File Segment: CPI; EPI

→ 1/5/3

DIALOG(R)File 352:Derwent WPI  
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014270872  
WPI Acc No: 2002-091573/200213  
Related WPI Acc No: 2002-149260  
XRAM Acc No: C02-028431

Composition for film formation, comprises product obtained by hydrolyzing  
and condensing at least one silane compound and an organic solvent